

## P-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 12	0.156 at V <sub>GS</sub> = - 4.5 V	1.18	6.7 nC
	0.190 at V <sub>GS</sub> = - 2.5V	1.07	
	0.245 at V <sub>GS</sub> = - 1.8V	0.49	

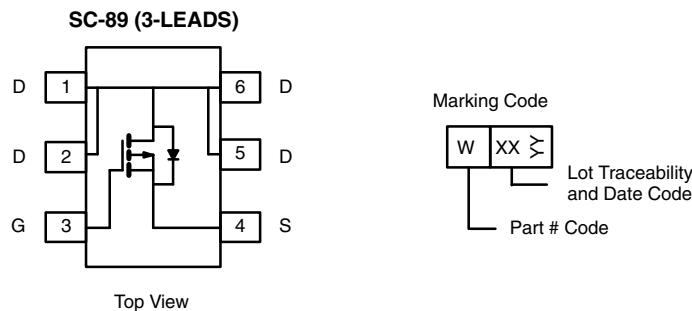
### FEATURES

- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- Material categorization:  
For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)

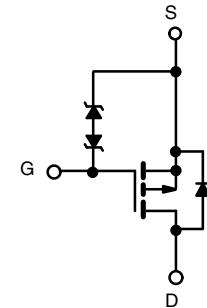


### APPLICATIONS

- Load Switch for Portable Devices



Ordering Information: Si1065X-T1-GE3 (Lead (Pb)-free and Halogen-free)



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	- 12	V	
Gate-Source Voltage	V <sub>GS</sub>	± 8		
Continuous Drain Current (T <sub>J</sub> = 150 °C)	I <sub>D</sub>	- 1.18 <sup>b, c</sup>	A	
		- 0.94 <sup>b, c</sup>		
Pulsed Drain Current	I <sub>DM</sub>	- 8		
Continuous Source-Drain Diode Current	I <sub>S</sub>	- 0.2 <sup>b, c</sup>		
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	0.236 <sup>b, c</sup>	W	
		0.151 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, b</sup>	R <sub>thJA</sub>	440	530	°C/W
		540	650	

Notes:

a. Maximum under steady state conditions is 650 °C/W.

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

**SPECIFICATIONS (T<sub>J</sub> = 25 °C, unless otherwise noted)**

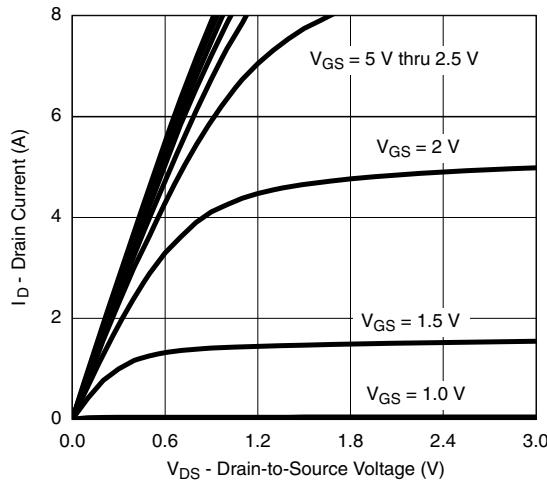
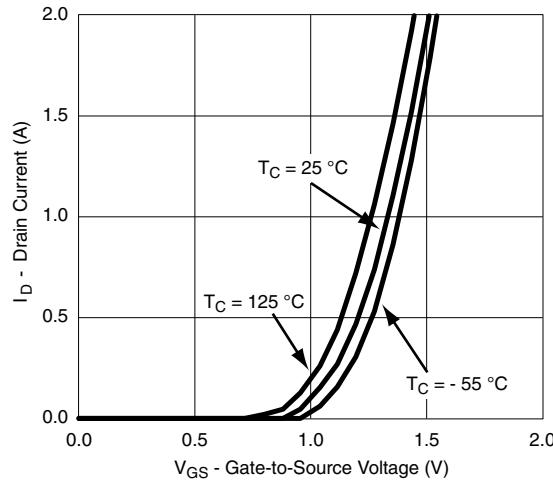
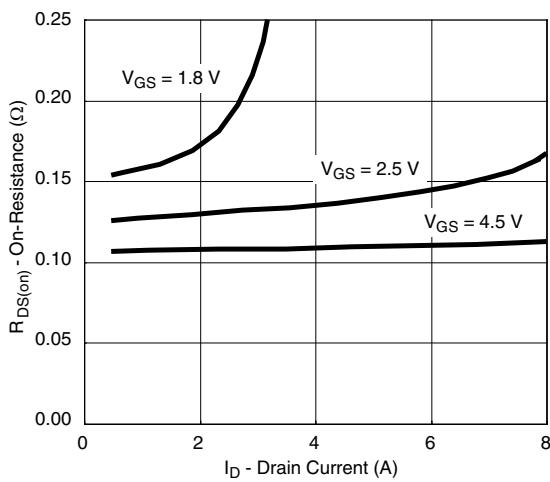
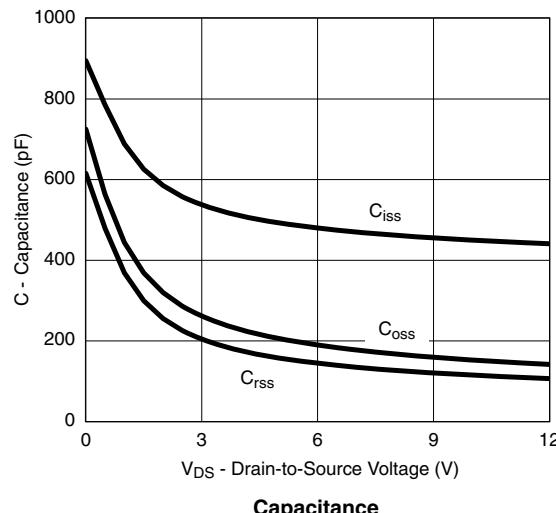
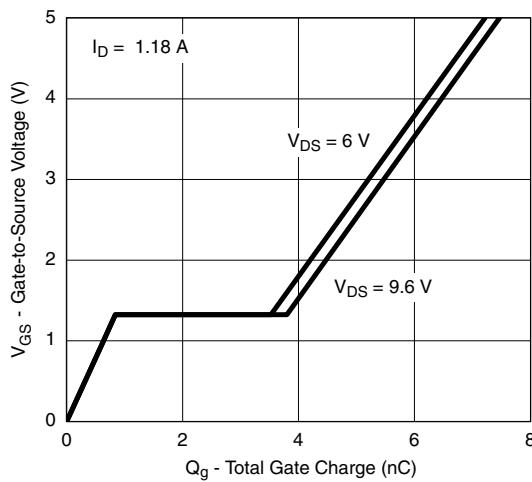
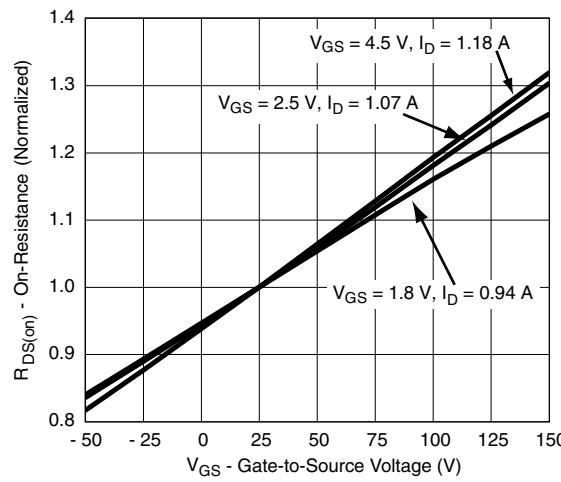
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 12			V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 8.47		mV/°C
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			2.33		
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.45		- 0.95	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 8 V			± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V			- 1	nA
		V <sub>DS</sub> = - 12 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 85 °C			- 10	μA
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = ≥ 5 V, V <sub>GS</sub> = - 4.5 V	- 8			A
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 1.18 A		0.108	0.156	Ω
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 1.07 A		0.131	0.190	
		V <sub>GS</sub> = - 1.8 V, I <sub>D</sub> = - 0.49 A		0.158	0.245	
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = - 6 V, I <sub>D</sub> = - 1.18 A		5.18		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = 0 V, f = 1 MHz		480		pF
Output Capacitance	C <sub>oss</sub>			190		
Reverse Transfer Capacitance	C <sub>rss</sub>			145		
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 6 V, V <sub>GS</sub> = - 5 V, I <sub>D</sub> = - 1.18 A		7.2	10.8	nC
Gate-Source Charge	Q <sub>gs</sub>			6.7	10.1	
Gate-Drain Charge	Q <sub>gd</sub>			0.84		
Gate Resistance	R <sub>g</sub>			2.7		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 6 V, R <sub>L</sub> = 6.32 Ω I <sub>D</sub> ≈ - 0.95 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		10	15	Ω
Rise Time	t <sub>r</sub>			13	19.5	ns
Turn-Off Delay Time	t <sub>d(off)</sub>			27	40.5	
Fall Time	t <sub>f</sub>			45	67.5	
				27	40.5	
<b>Drain-Source Body Diode Characteristics</b>						
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>	I <sub>F</sub> = - 0.7 A, dI/dt = 100 A/μs			8	A
Body Diode Voltage	V <sub>SD</sub>		I <sub>S</sub> = - 0.63 A		0.8	1.2
Body Diode Reverse Recovery Time	t <sub>rr</sub>				29.2	44
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>				10.22	15.3
Reverse Recovery Fall Time	t <sub>a</sub>				13.7	
Reverse Recovery Rise Time	t <sub>b</sub>				15.5	

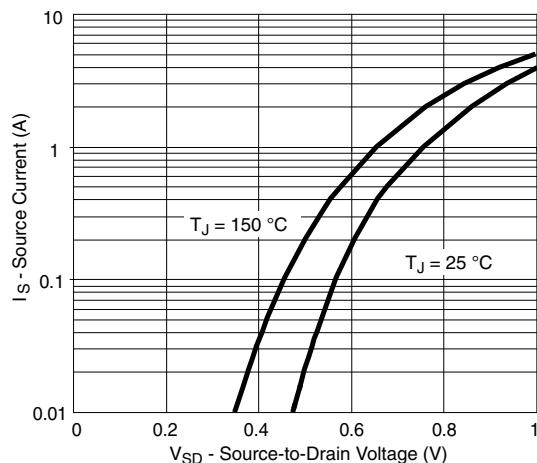
Notes:

a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2 %.

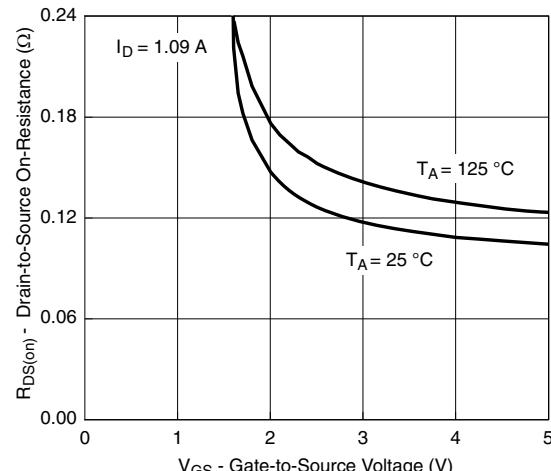
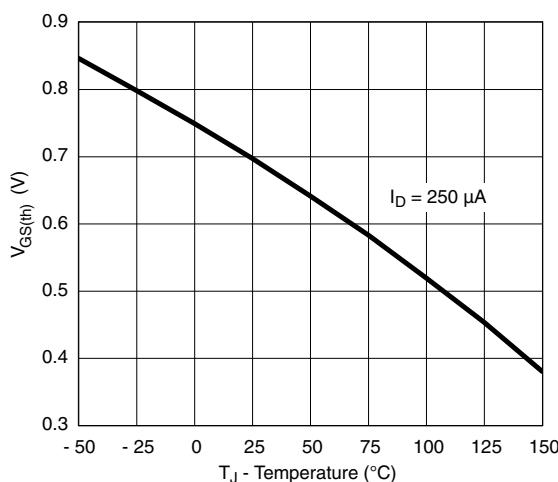
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

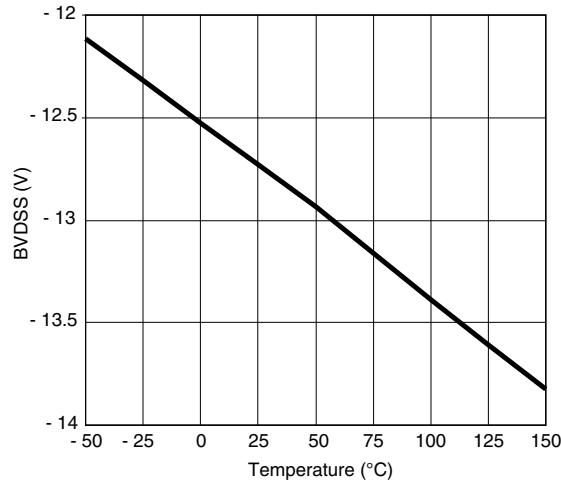
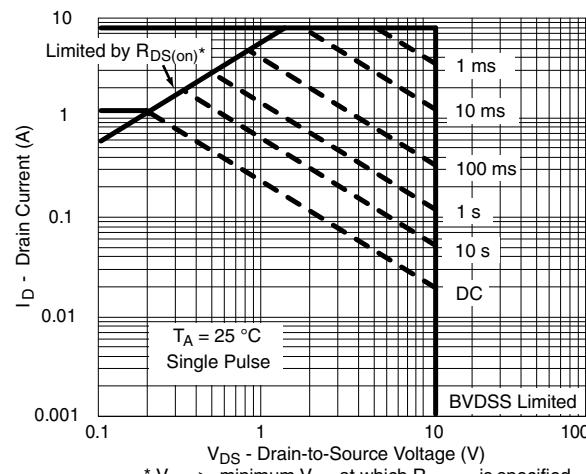
**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics Curves vs. Temp.**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)


Source-Drain Diode Forward Voltage

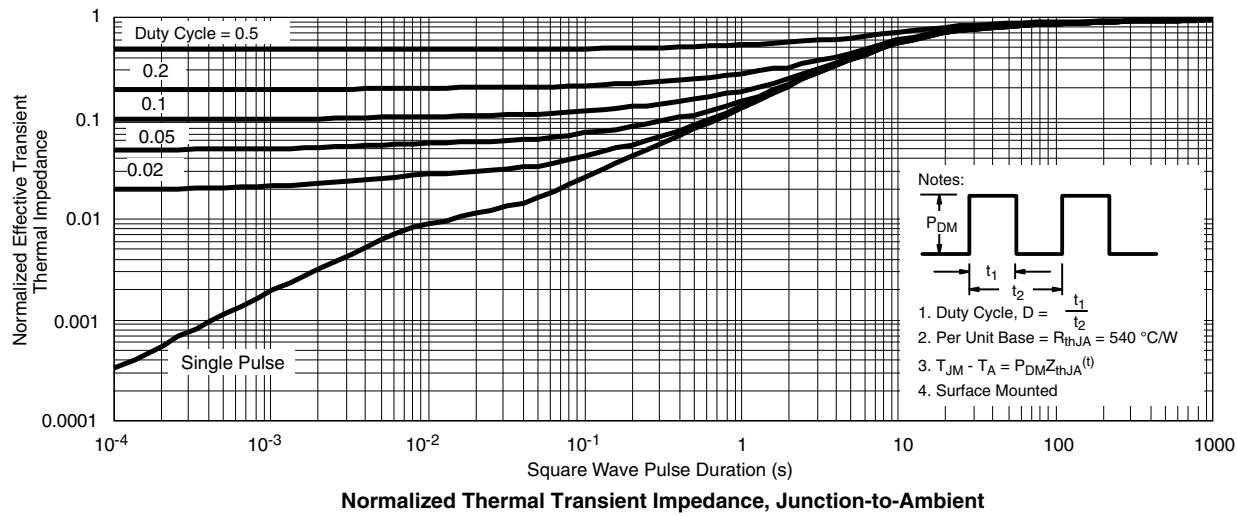
 $R_{DS(on)}$  vs.  $V_{GS}$  vs. Temperature

Threshold Voltage

 $BV_{DS}$  vs. Temperture

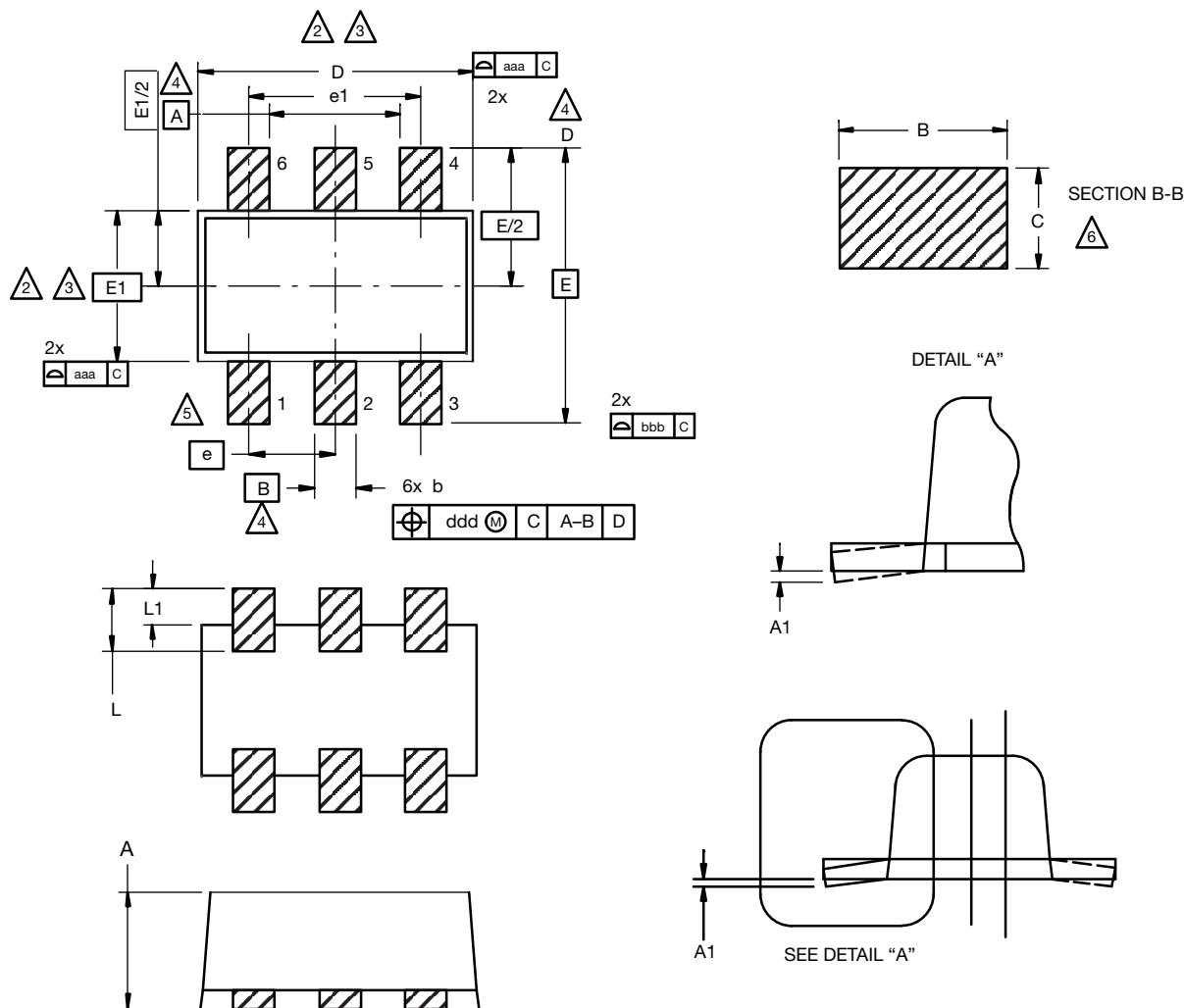
Safe Operating Area, Junction-to-Ambient

**TYPICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$ , unless otherwise noted)



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### SC-89 6-Leads (SOT-563F)



#### Notes

1. Dimensions in millimeters.

 Dimension D does not include mold flash, protrusions or gate burrs. Mold flush, protrusions or gate burrs shall not exceed 0.15 mm per dimension E1 does not include interlead flash or protrusion, interlead flash or protrusion shall not exceed 0.15 mm per side.

 Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, the bar burrs, gate burrs and interlead flash, but including any mismatch between the top and the bottom of the plastic body.

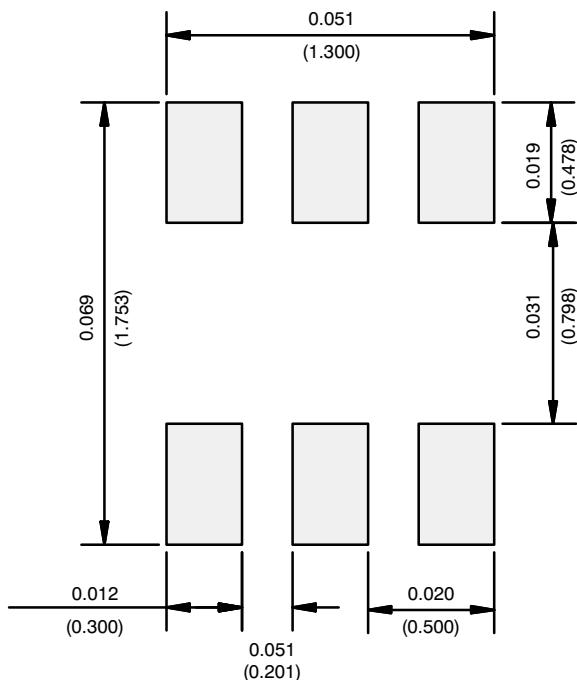
 Datums A, B and D to be determined 0.10 mm from the lead tip.

 Terminal numbers are shown for reference only.

 These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.56	0.58	0.60
A1	0	0.02	0.10
b	0.15	0.22	0.30
c	0.10	0.14	0.18
D	1.50	1.60	1.70
E	1.50	1.60	1.70
E1	1.15	1.20	1.25
e	0.45	0.50	0.55
e1	0.95	1.00	1.05
L	0.25	0.35	0.50
L1	0.10	0.20	0.30

C14-0439-Rev. C, 11-Aug-14  
DWG: 5880

**RECOMMENDED MINIMUM PADS FOR SC-89: 6-Lead**

Recommended Minimum Pads  
Dimensions in Inches/(mm)

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